

DATA SHEET

PDTC124T series
NPN resistor-equipped transistors;
R1 = 22 k Ω , R2 = open

Product specification
Supersedes data of 2003 Jan 20

2003 Apr 10

**NPN resistor-equipped transistors;
R1 = 22 kΩ, R2 = open**
PDTC124T series
FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–	50	V
I_o	output current (DC)	–	100	mA
R1	bias resistor	22	–	kΩ
R2	open	–	–	–

DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE
	PHILIPS	EIAJ	
PDTC124TEF	SOT490	SC-89	35
PDTC124TK	SOT346	SC-59	50
PDTC124TM	SOT883	SC-101	DZ
PDTC124TS	SOT54 (TO-92)	SC-43	TC124T
PDTC124TT	SOT23	–	*45 ⁽¹⁾
PDTC124TU	SOT323	SC-70	*50 ⁽¹⁾

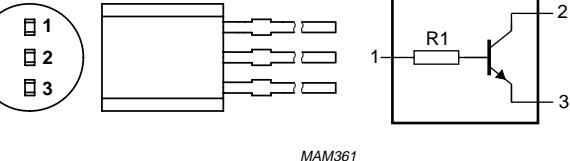
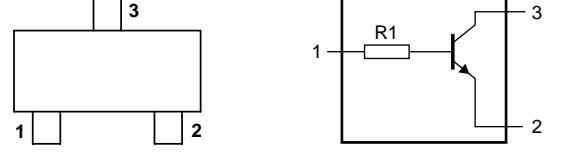
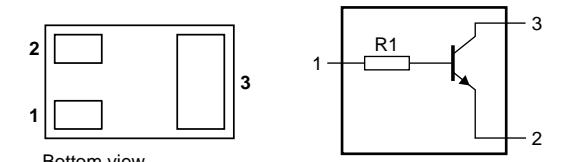
Note

1. * = p: Made in Hong Kong.
- * = t: Made in Malaysia.
- * = W: Made in China.

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PDTC124T series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC124TS	 <p>MAM361</p>	1 2 3	base collector emitter
PDTC124TEF PDTC124TK PDTC124TT PDTC124TU	 <p>Top view</p> <p>MDB270</p>	1 2 3	base emitter collector
PDTC124TM	 <p>Bottom view</p> <p>MHC507</p>	1 2 3	base emitter collector

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	50	V
V_{CEO}	collector-emitter voltage	open base	–	50	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_o	output current (DC)		–	100	mA
I_{CM}	peak collector current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT490	notes 1 and 2	–	250	mW
	SOT883	notes 2 and 3	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 µm copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

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CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	–	–	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0	–	–	1	μA
		V _{CE} = 30 V; I _B = 0; T _j = 150 °C	–	–	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	–	–	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA	100	–	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	–	–	150	mV
R1	input resistor		15.4	22	28.6	kΩ
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz	–	–	2.5	pF

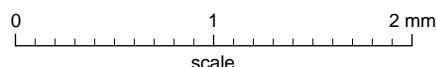
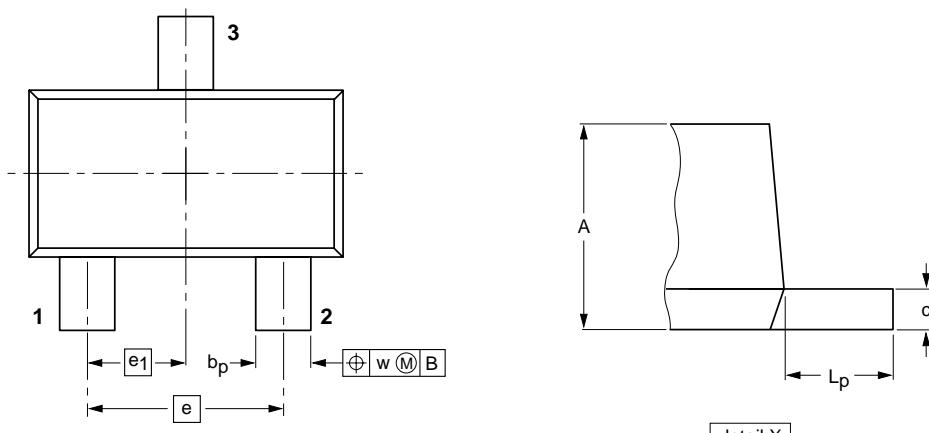
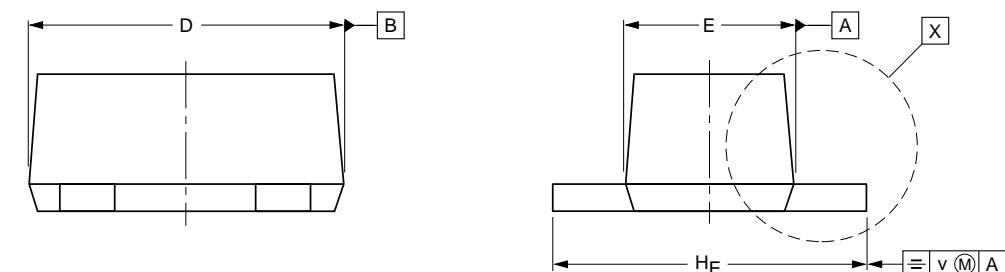
NPN resistor-equipped transistors;
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PDTC124T series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT490



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	H _E	L _p	v	w
mm	0.8	0.33	0.2	1.7	0.95	1.0	0.5	1.7	0.5	0.1	0.1
	0.6	0.23	0.1	1.5	0.75			1.5	0.3		

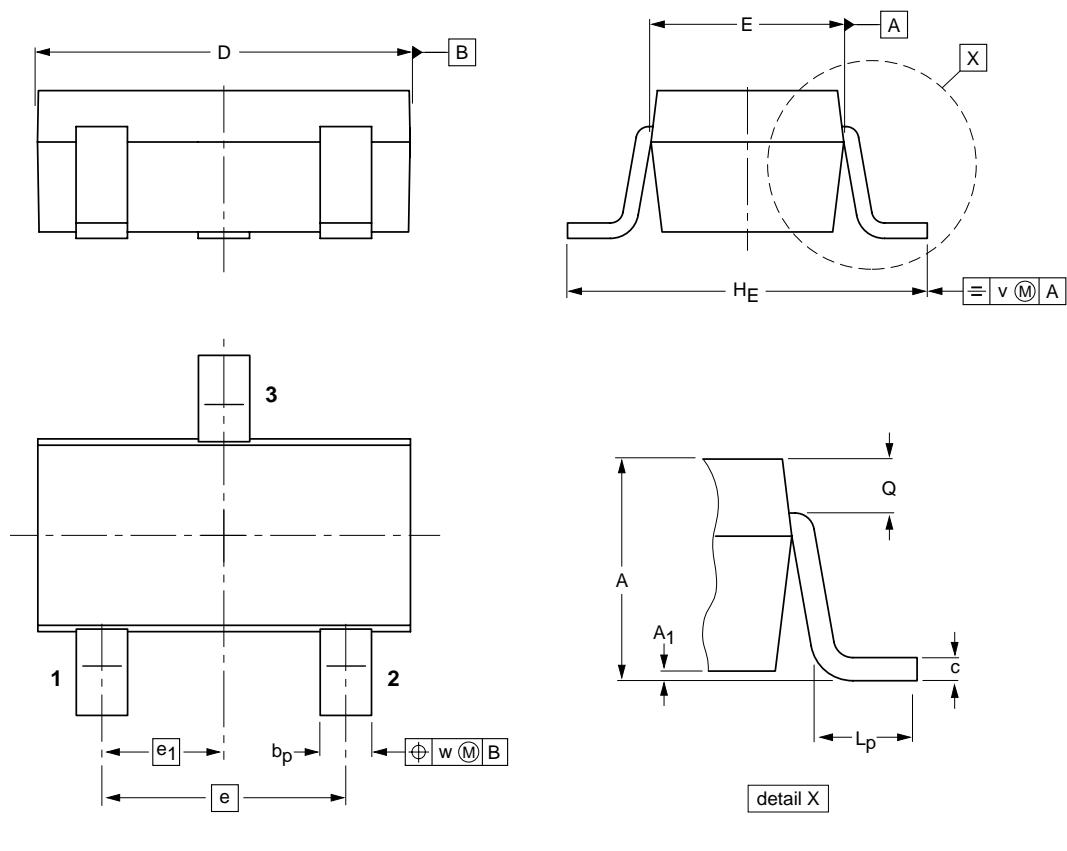
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT490			SC-89			98-10-23

NPN resistor-equipped transistors;
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PDTC124T series

Plastic surface mounted package; 3 leads

SOT346



0 1 2 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.3	0.1	0.50	0.26	3.1	1.7	1.9	0.95	3.0	0.6	0.33	0.2	0.2
	1.0	0.013	0.35	0.10	2.7	1.3	1.9	0.95	2.5	0.2	0.23		

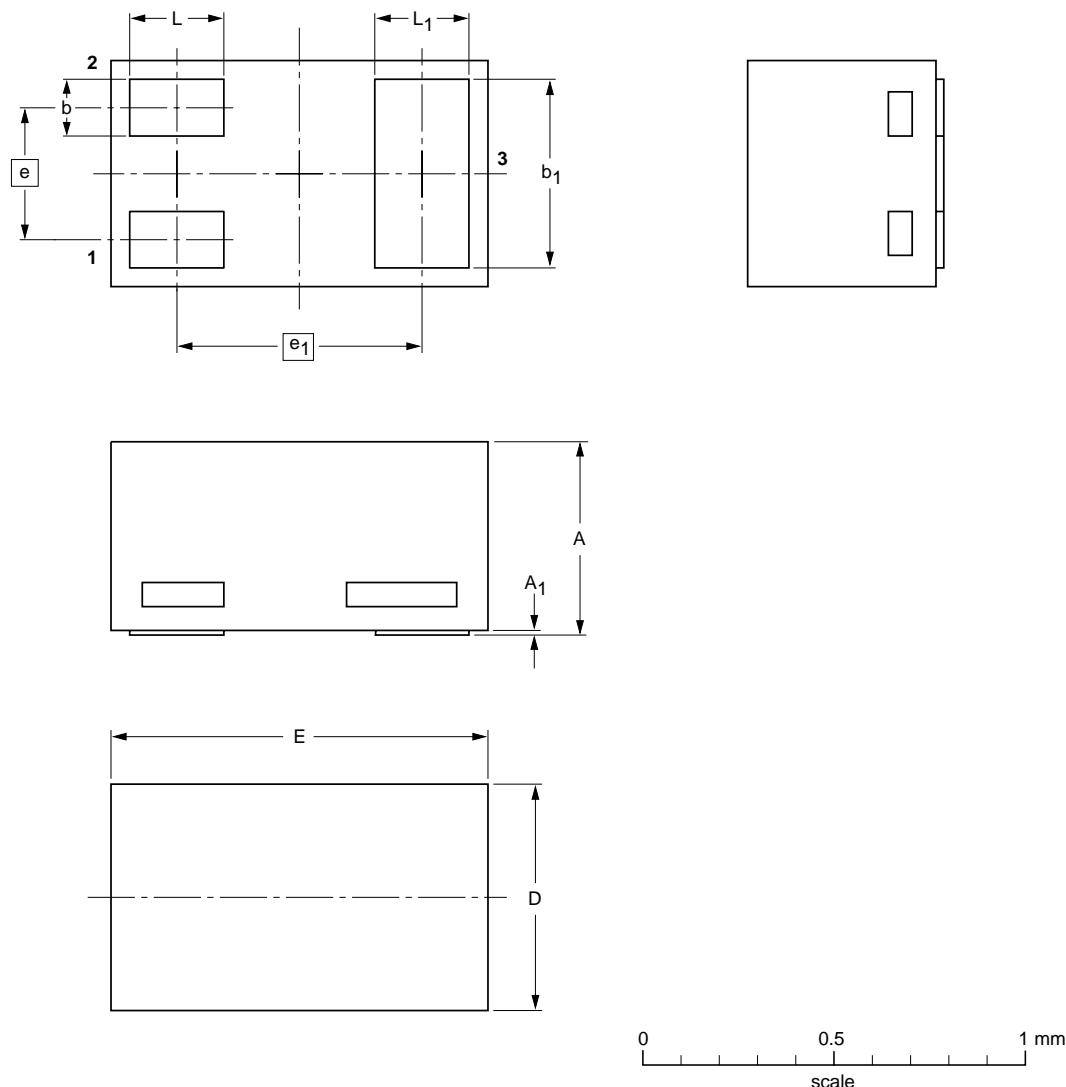
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT346		TO-236	SC-59			98-07-17

NPN resistor-equipped transistors;
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PDTC124T series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾	A ₁ max.	b	b ₁	D	E	e	e ₁	L	L ₁
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

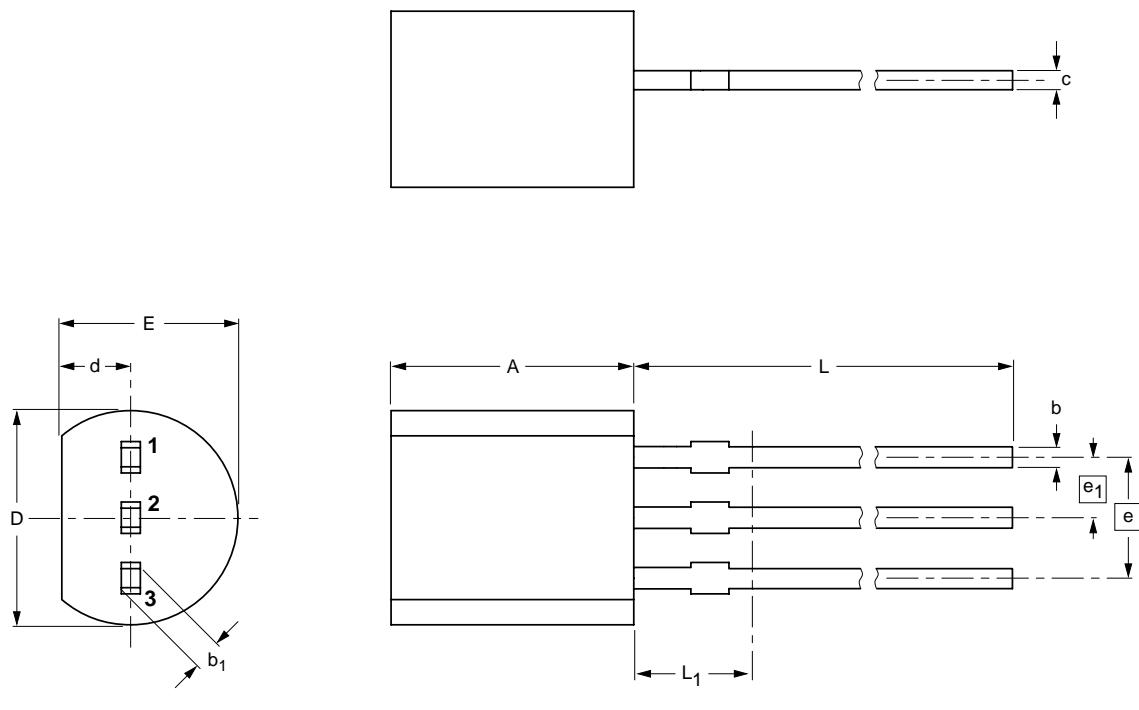
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA	SC-101		
SOT883						03-02-05 03-04-03

NPN resistor-equipped transistors;
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Plastic single-ended leaded (through hole) package; 3 leads

SOT54



0 2.5 5 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾
mm	5.2	0.48	0.66	0.45	4.8	1.7	4.2	2.54	1.27	14.5	
	5.0	0.40	0.56	0.40	4.4	1.4	3.6			12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

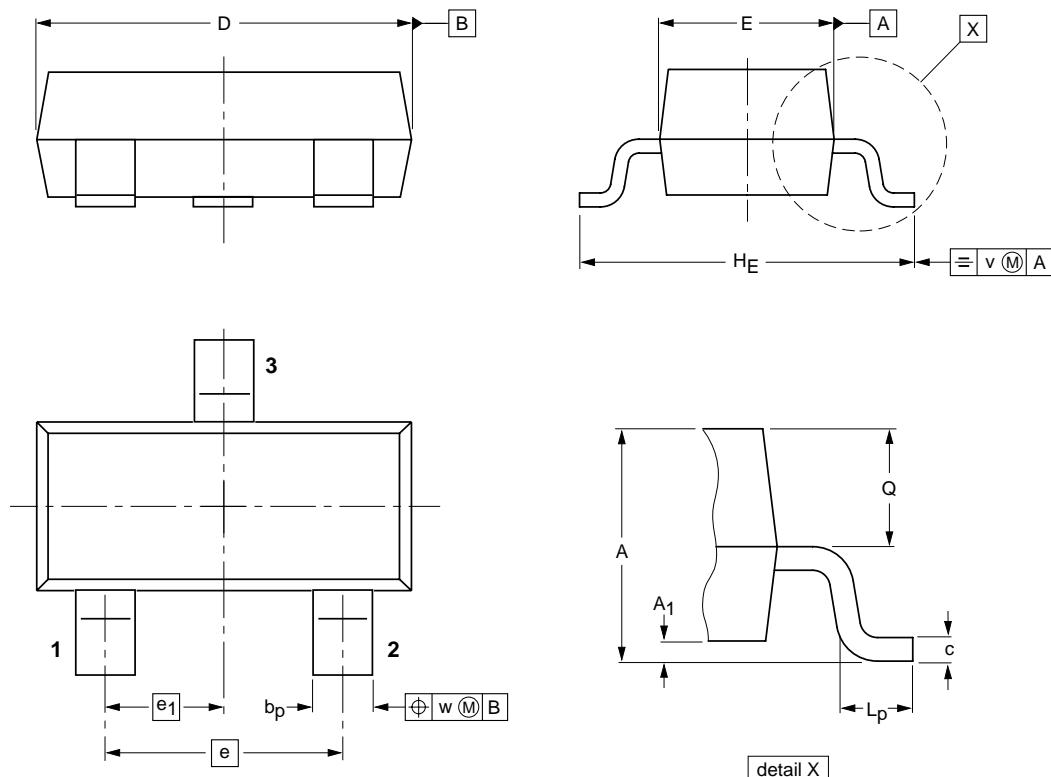
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT54		TO-92	SC-43			97-02-28

NPN resistor-equipped transistors;
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Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

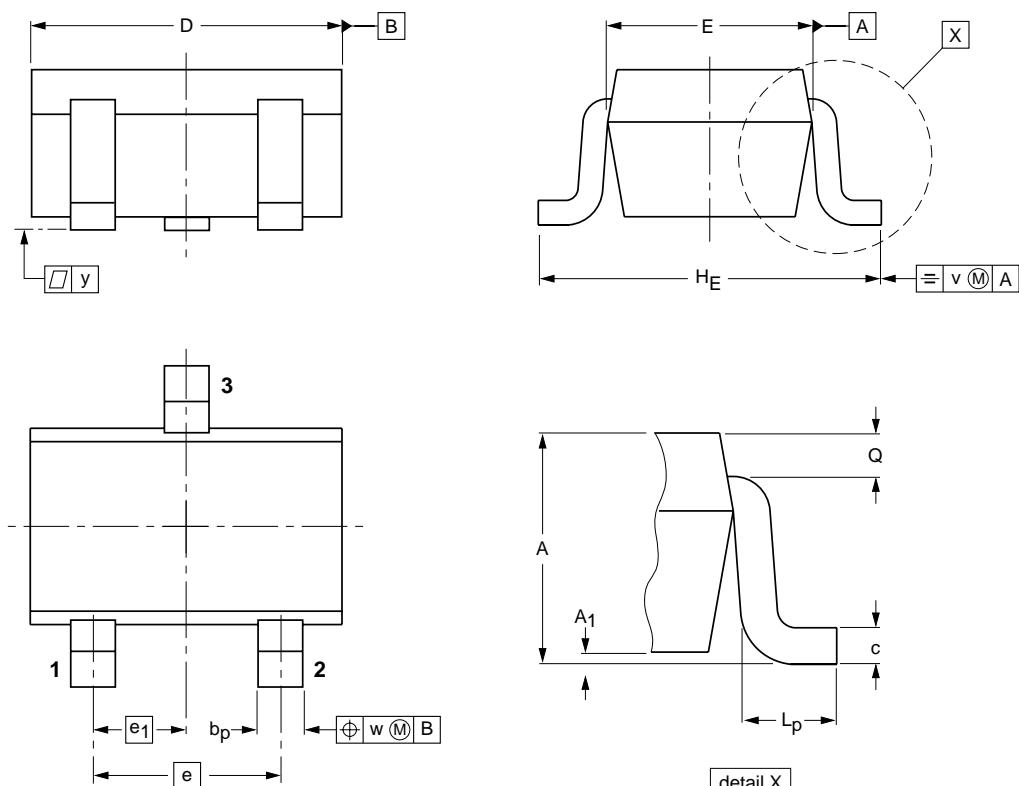
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				-97-02-28 99-09-13

NPN resistor-equipped transistors;
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Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ	SC-70		
SOT323						97-02-28

NPN resistor-equipped transistors;
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PDTC124T series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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NOTES

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